

L Number	Hits	Search Text	DB	Time stamp
1	2	("5734182").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:28
2	4840	GaN and In	USPAT	2004/03/02 11:28
3	3387	GaN and In and (substrate and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:30
4	2206	GaN and In and (substrate and electrode) and ((p and n) near3 type)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:30
5	1516	GaN and In and (substrate and electrode) and ((p and n) near3 type) and buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:30
6	1126	GaN and In and (substrate and electrode) and ((p and n) near3 type) and buffer and (active near3 (region or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:31
7	160	372/45.ccls. and (GaN and In and (substrate and electrode) and ((p and n) near3 type) and buffer and (active near3 (region or layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:32
8	200	372/45-50.ccls. and (GaN and In and (substrate and electrode) and ((p and n) near3 type) and buffer and (active near3 (region or layer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:33
9	182	372/45-50.ccls. and (GaN and In and (substrate and electrode) and ((p and n) near3 type) and buffer and (active near3 (region or layer)) and (temperature))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:35
10	108	372/45-50.ccls. and (GaN and In and (substrate and electrode) and ((p and n) near3 type) and buffer and (active near3 (region or layer)) and (temperature) and conductivity)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 12:15
11	2	("5670798") or ("5625202")).PN.	USPAT	2004/03/02 12:16
12	5	("4801984" "5294833" "5351255" "5366927" "5385862").PN.	USPAT	2004/03/02 12:16
13	9	("3857054" "4221981" "4792467" "5006908" "5162930" "5274251" "5300793" "5341001" "5385862").PN.	USPAT	2004/03/02 12:16
-	23	("0496030") or ("0541373") or ("4209577") or ("4236478") or ("5110138") or ("5343802") or ("7335975") or ("6041478") or ("62165991") or ("6417484") or ("7263749") or ("7273069") or ("7273366") or ("7288334") or ("7235729") or ("0783136") or ("7254733") or ("7263748") or ("7106633") or ("7122520") or ("7131068") or ("7131069")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/02 11:24
-	4657	electrode and substrate and (GaN or (gallium adj3 nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 19:48
-	2321	electrode and substrate and (GaN or (gallium adj3 nitride)) and buffer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 19:48
-	2059	electrode and substrate and (GaN or (gallium adj3 nitride)) and buffer and In	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 19:49
-	964	electrode and substrate and (GaN or (gallium adj3 nitride)) and buffer and In and InGaN	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 19:49

-	959	electrode and substrate and (GaN or (gallium adj3 nitride)) and buffer and (In and InGaN and GaN)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 19:50
-	818	electrode and substrate and (GaN or (gallium adj3 nitride)) and buffer and (In and InGaN) and temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 19:50
-	426	electrode and substrate and (GaN or (gallium adj3 nitride)) and buffer and (In and InGaN) and temperature and (p adj3 type near3 contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 19:51
-	3669	372/45.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:01
-	6635	372/43,75.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:02
-	3707	372/46,44.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 19:59
-	220	372/46,44.ccls. and (InGaN or GaN or GaInN)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:00
-	193	372/46,44.ccls. and ((InGaN or GaN or GaInN) and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:00
-	100	372/43,75.ccls. and ((InGaN or GaN or GaInN) and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:00
-	240	372/45.ccls. and ((InGaN or GaN or GaInN) and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:01
-	240	372/45.ccls. and ((InGaN or GaN or GaInN) and electrode and substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:01
-	13616	372/40-50.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:02
-	396	372/40-50.ccls. and ((InGaN or GaN or GaInN) and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:02
-	6	("4347611" "4567060" "4890293" "4982409" "5210767" "5218613").PN.	USPAT	2004/02/26 20:22
-	13	5751752.URPN.	USPAT	2004/02/26 20:23
-	172	shakuda adj3 yukio.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:36
-	172	shakuda adj3 yukio.inv. and (semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/26 20:36